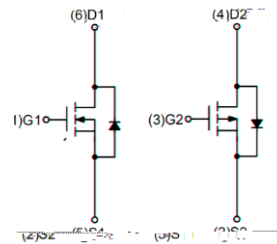


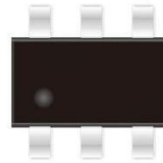
It combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. It combines one N Channel MOSFET and one P channel MOSFET.

Product Summary



Trench technology

- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Dual DIE in one package



- Power Management in Notebook Computer
- BLDC Motor driver

	ZMC88212U
	88212
	REEL TAPE
	3000

N Channel Absolute Maximum Ratings $T_C = 25$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current	$I_{D@T_C=25}$	4	A
	$I_{D@T_C=75}$	3	A
	$I_{D@T_C=100}$	2.5	A
Pulsed Drain Current	I_{DM}	12	A
Total Power Dissipation	$P_D@T_C=25$	2.1	W
Total Power Dissipation	$P_D@T_A=25$	1.25	W
Operating Junction Temperature	T_J	-55 to 150	
Storage Temperature	T_{STG}	-55 to 150	
Single Pulse Avalanche Energy	E_{AS}	5	mJ



N Channel characteristics curve

Fig.1 Power Dissipation



Fig.2 Typical output Characteristics

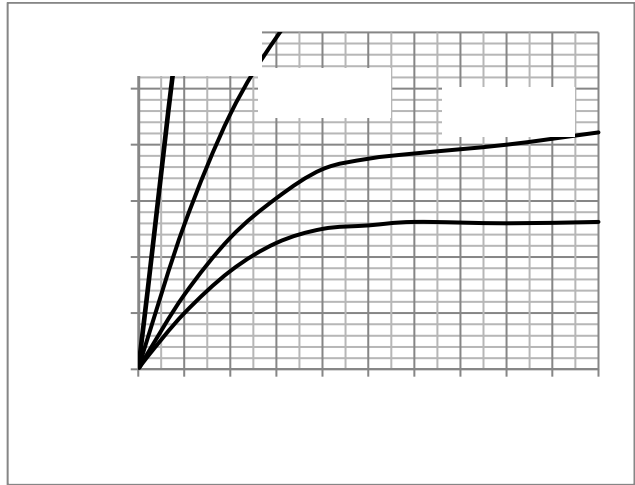


Fig.3 Threshold Voltage V.S Junction Temperature

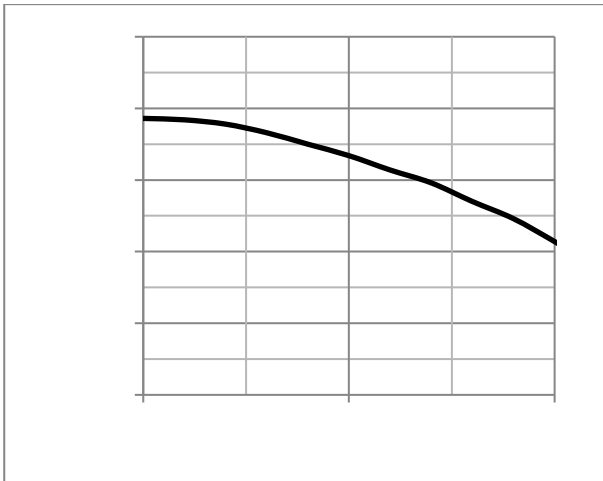


Fig.4 Resistance V.S Drain Current

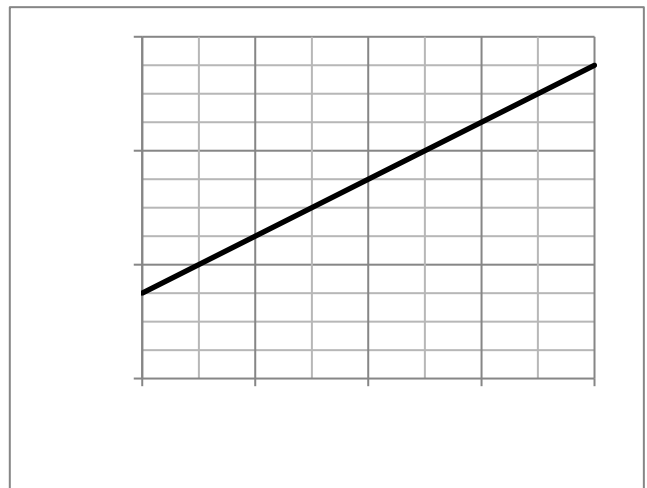
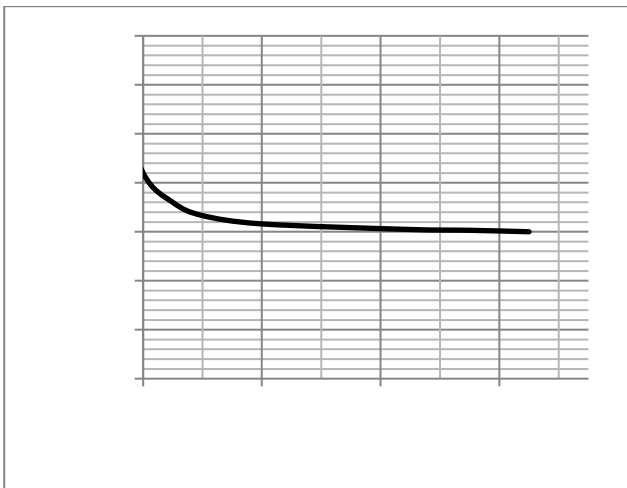




Fig.3 Threshold Voltage V.S Junction Temperature Fig.4 Resistance V.S Drain Current

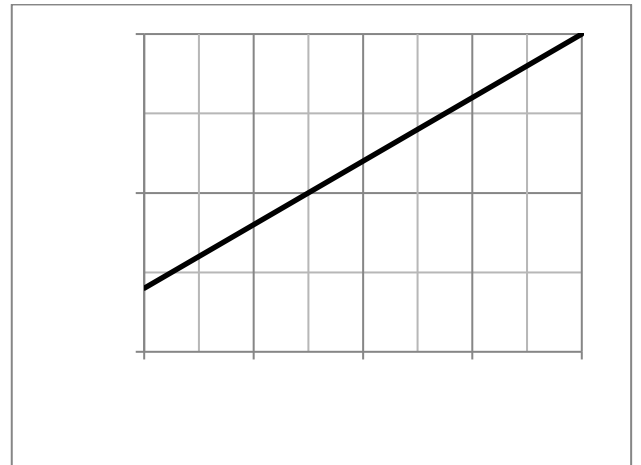
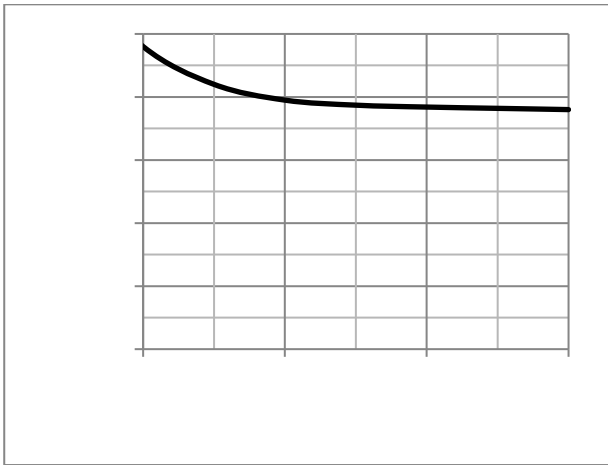
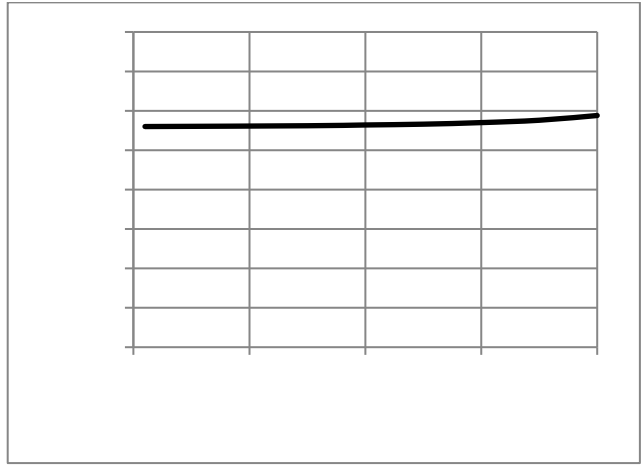
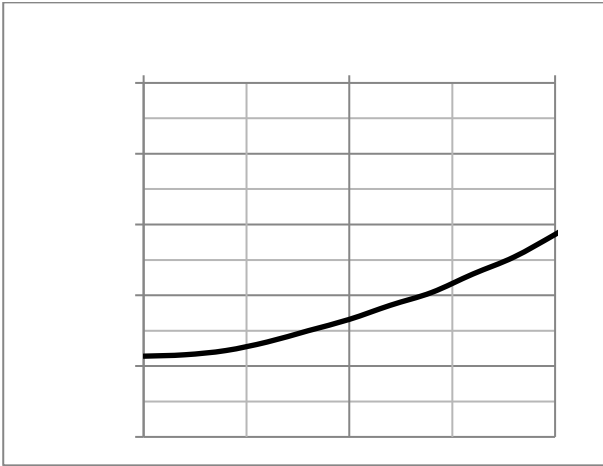


Fig.7 Gate-Charge Characteristics

Fig.8 Capacitance Characteristics

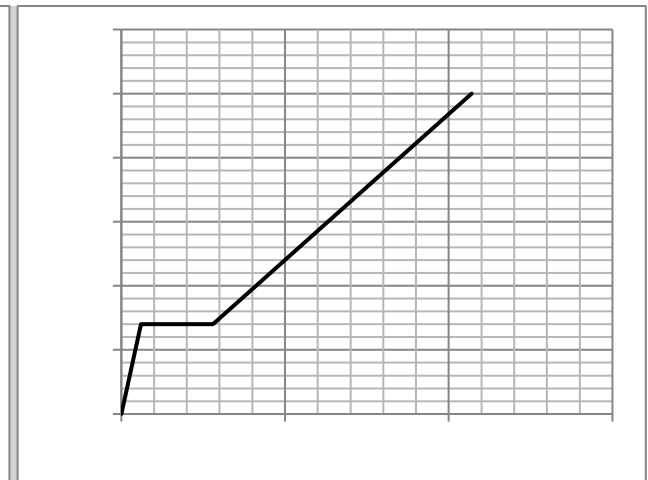
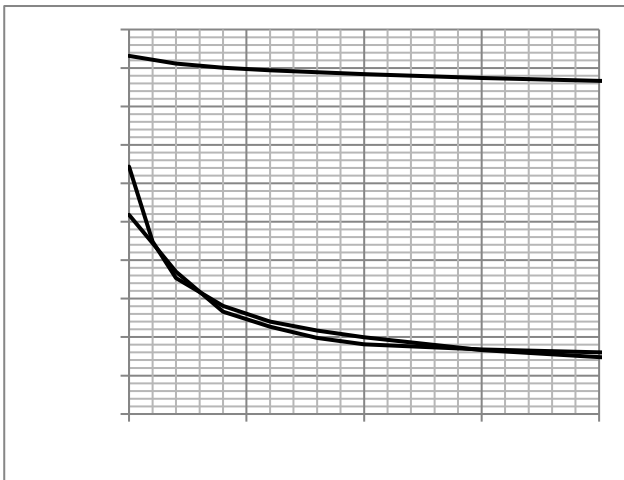


Fig.9 SOA Maximum Safe Operating Area

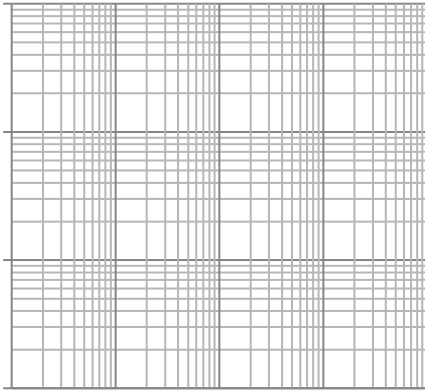
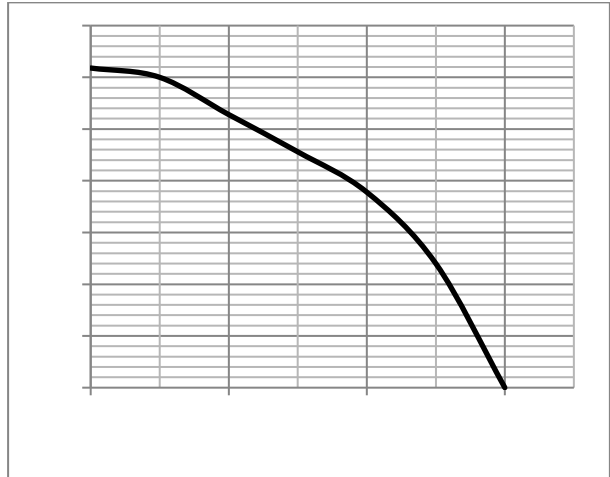


Fig.10 ID-Junction Temperature



Test Circuit

Fig.1 Switching Time Measurement Circuit

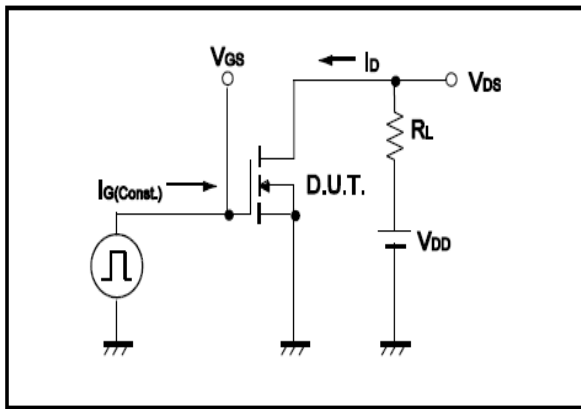


Fig.2 Gate Charge Waveform

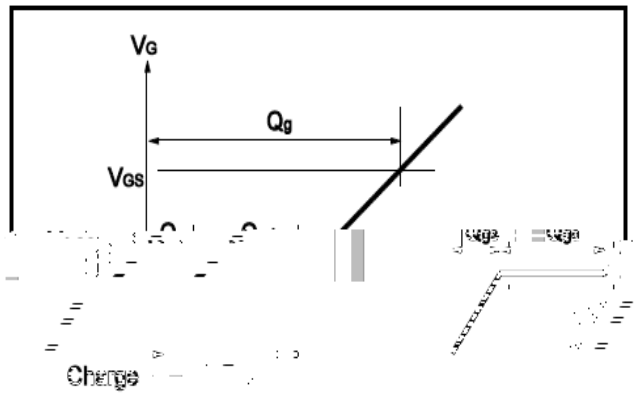


Fig.3 Switching Time Measurement Circuit

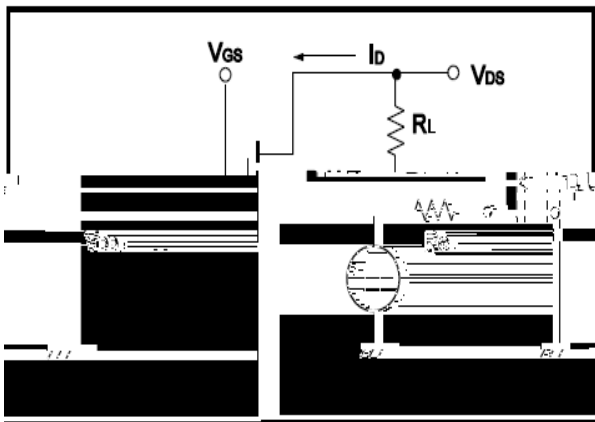


Fig.4 Gate Charge Waveform

